

IN THE SPECIFICATION:

Please replace paragraph number [0014] with the following rewritten paragraph:

[0014] During conventional back surface-grinding treatments, a semiconductor wafer is thinned to a desired thickness by the mechanical action of a grinding wheel. In processing the semiconductor wafer, the circuit pattern-formed surface (the “active surface”) of the wafer is prevented from being stained or injured with grinding trashes, etc., by a protective member or submount previously adhered to the circuit pattern-formed surface of the wafer via an automatic adhering apparatus. After applying the back ~~surface~~surface-grinding treatment, the protective member may remain or may be peeled off or dislodged, and the semiconductor wafer is sent to a subsequent dicing process. To support and transport the wafer for dicing, a carrier tape or film is typically applied to the back surface of the wafer. Following dicing, the semiconductor dice are marked with identifying information, and either stored, transported, or mounted on carrier substrates such as leadframes or circuit boards which will be populated with an individual semiconductor die or semiconductor dice. The carrier tape or film applied prior to dicing is typically removed during the pick-and-place process of attaching singulated dice to the desired carrier substrate.

Please replace paragraph number [0039] with the following rewritten paragraph:

[0039] Laser-markable tape 1 preferably has an adhesive layer 2 formed on at least one side thereof, allowing laser-markable tape 1 to be temporarily or permanently adhered to a surface on the back side surface 12 of semiconductor wafer 10, the level of adherence dependent upon the tape-laser application. Alternatively, an adhesive may be applied directly to a back side surface 12 of the semiconductor wafer 10 by spray, spin-on or deposition processes and the like. Adhesive layer 2 may comprise a pressure-sensitive adhesive, radiation-curable adhesive, B-stage epoxy, or any other adhesive variety known in the art with bonding strength and other characteristics consistent with the type of tape used for the purposes of the invention. For example, in applications where semiconductor die 20 is to be marked by ablation of one or more layers of marking tape 1 with a laser, an adhesive layer with permanent adherence to the die surface may be used for which various epoxy resins or other adhesives known in the art will

prove suitable. In applications where inks, dyes, or paints embedded within or coating marking tape 1 are to be transferred to a surface of semiconductor die 20, marking tape 1 need only temporarily bond to semiconductor die 20 until the mark transfer takes place. Thereafter, marking tape 1 can be peeled or otherwise removed from the surface of semiconductor die 20. Laser-markable adhesive layers which are contemplated for use in the present invention include, but are not limited to, UV acrylics, thiolene, poly-paraxylylene (Paralene), urethanes, silicones, epoxies, and acrylics.

Please replace paragraph number [0048] with the following rewritten paragraph:

[0048] In another preferred embodiment, carrier tape 4 can be used in conjunction with one or more levels of adhesives, at least one of the adhesives comprising laser-markable components when disposed on a surface of a bare semiconductor die 20. In one embodiment, a markable adhesive layer ~~2B~~ 1B serves to bind carrier tape 4 to a bare surface on the backside 12 of semiconductor wafer 10, and will transfer a laser-markable residue to a surface of semiconductor die 20 when carrier tape 4 is later removed. In this case, carrier tape 4 functions to provide a support and protective function during semiconductor processing, but can be peeled away to effect transfer of the laser-markable residue.